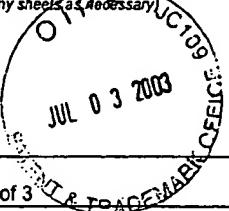


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		Application Number	09/484303			
		Filing Date	January 18, 2000			
		First Named Inventor	Ahn, Kie			
		Group Art Unit	2823			
		Examiner Name	Berezny, Neal			
Sheet 1 of 3		Attorney Docket No: 303.648US1				

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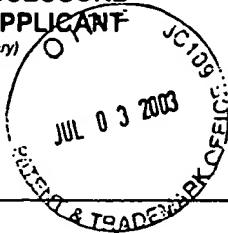
\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

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## STATEMENT BY APPLICANT

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Examiner Name	Berezny, Neal

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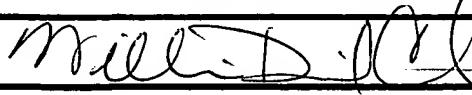
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		Group Art Unit	2823
		Examiner Name	Berezny, Neal
Sheet 3 of 3		Attorney Docket No: 303.648US1	

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